

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3439889	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:08
L2	32	1 and (high adj k or high adj dielectric) with between with floating adj gate with (channel or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:10
L3	9	2 and (charg\$5 or electron or hole or carrier) with (transfer\$5 or mov\$5 or inject\$5 or eject\$5) with floating adj gate with control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:19
L4	495	1 and part\$5 with (isolat\$5 or insulat\$5 or dielectric) with floating adj gate with channel	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:19
L5	149	4 and (charg\$5 or electron or hole or carrier) with (transfer\$5 or mov\$5 or inject\$5 or eject\$5) with floating adj gate with control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:20
L6	0	4 and (charg\$5 or electron or hole or carrier) with (transfer\$5 or mov\$5 or inject\$5 or eject\$5) with floating adj gate near3 control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:20

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L1	39	((memory or storage) and high adj k and floating adj gate and control adj gate and between).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:46
L2	11	((memory or storage) and high adj k and floating adj gate and control adj gate and between and channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 20:46